SEMICONDUCTORS

## ZXTP07040DFF <br> 40V, SOT23F, PNP medium power transistor

## Summary;

$B V_{\text {CEO }}>-40 \mathrm{~V}$
$B V_{E C O}>-3 V$
$I_{\text {(cont) }}=-3 \mathrm{~A}$
$\mathrm{V}_{\mathrm{CE} \text { (sat) }}<-100 \mathrm{mV}$ @ 1A
$R_{\text {CE(sat) }}=67 \mathrm{~m} \Omega$
$\mathrm{P}_{\mathrm{D}}=1.5 \mathrm{~W}$


## Complementary part number ZXTN07045EFF

## Description

This low voltage PNP transistor has been designed for applications requiring high gain and very low saturation voltage. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

## Features



- Low profile SOT23F package
- Low saturation voltage
- High Gain
- High power dissipation


## Applications

- Load switches
- Battery charging
- Siren driver


Pinout - top view

- MOSFET and IGBT gate driver
- Motor drive


## Ordering information

| Device | Reel size <br> (inches) | Tape width <br> (mm) | Quantity <br> per reel |
| :--- | :---: | :---: | :---: |
| ZXTP07040DFFTA | 7 | 8 | 3000 |

## Device marking

## ZXTP07040DFF

## Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
| :---: | :---: | :---: | :---: |
| Collector-base voltage | $\mathrm{V}_{\text {CBO }}$ | -50 | V |
| Collector-emitter voltage | $\mathrm{V}_{\text {CEO }}$ | -40 | V |
| Emitter-collector voltage (reverse blocking) | $\mathrm{V}_{\text {ECO }}$ | -3 | V |
| Emitter-base voltage | $\mathrm{V}_{\text {EBO }}$ | -7 | V |
| Continuous collector current ${ }^{(\mathrm{c})}$ | $\mathrm{I}_{\mathrm{C}}$ | -3 | A |
| Peak pulse current | $\mathrm{I}_{\text {CM }}$ | -6 | A |
| Base current | $\mathrm{I}_{\mathrm{B}}$ | -1 | A |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{(\mathrm{a})}$ Linear derating factor | $\mathrm{P}_{\mathrm{D}}$ | $\begin{aligned} & 0.84 \\ & 6.72 \end{aligned}$ | W $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{(b)}$ Linear derating factor | $\mathrm{P}_{\mathrm{D}}$ | $\begin{gathered} 1.34 \\ 10.72 \end{gathered}$ | W $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$ (c) Linear derating factor | $\mathrm{P}_{\mathrm{D}}$ | $\begin{aligned} & 1.50 \\ & 12.0 \end{aligned}$ | W $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$ (d) <br> Linear derating factor | $\mathrm{P}_{\mathrm{D}}$ | $\begin{gathered} \hline 2.0 \\ 16.0 \end{gathered}$ | W $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Operating and storage temperature range | $\mathrm{T}_{\mathrm{j}}, \mathrm{T}_{\text {stg }}$ | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |

## Thermal resistance

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Junction to ambient $^{(\mathrm{a})}$ | $\mathrm{R}_{\Theta J A}$ | 149 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{(\mathrm{b})}$ | $\mathrm{R}_{\text {ӨJA }}$ | 93 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{(\mathrm{c})}$ | $\mathrm{R}_{\text {ӨJA }}$ | 83 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{\text {(d) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 60 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## NOTES:

(a) For a device surface mounted on $15 \mathrm{~mm} \times 15 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with high coverage of single sided 10 c copper, in still air conditions.
(b) Mounted on $25 \mathrm{~mm} \times 25 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(c) Mounted on $50 \mathrm{~mm} \times 50 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(d) As (c) above measured at $\mathrm{t}<5 \mathrm{secs}$.

## ZXTP07040DFF

## Characteristics




Transient Thermal Impedance



Pulse Power Dissipation

## ZXTP07040DFF

## Electrical characteristics (at $\mathrm{T}_{\mathrm{amb}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
| :--- | :--- | :---: | :---: | :---: | :---: | :--- |
| Collector-base breakdown <br> voltage | $\mathrm{BV}_{\mathrm{CBO}}$ | -50 | -80 |  | V | $\mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A}$ |
| Collector-emitter breakdown <br> voltage (base open) | $\mathrm{BV}_{\mathrm{CEO}}$ | -40 | -65 |  | V | $\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}^{\left({ }^{*}\right)}$ |
| Emitter-base breakdown <br> voltage | $\mathrm{BV}_{\mathrm{EBO}}$ | -7 | -8.3 |  | V | $\mathrm{I}_{\mathrm{E}}=-100 \mu \mathrm{~A}$ |
| Emitter-collector breakdown <br> voltage (reverse blocking) | $\mathrm{BV}_{\mathrm{ECO}}$ | -3 | -8.6 |  | V | $\mathrm{I}_{\mathrm{E}}=-100 \mu \mathrm{~A}$ |
| Collector-base cut-off current | $\mathrm{I}_{\mathrm{CBO}}$ |  | $<-1$ | -50 | nA | $\mathrm{V}_{\mathrm{CB}}=-36 \mathrm{~V}$ |
|  |  |  |  | -1 | -50 | nA |

NOTES:
(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu \mathrm{~s}$; duty cycle $\leq 2 \%$.

## ZXTP07040DFF

## Typical characteristics




## ZXTP07040DFF

## Package outline - SOT23F



| Dim. | Millimeters |  | Inches |  | Dim. | Millimeters |  | Inches |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Max. | Min. | Max. |  | Min. | Max. | Max. | Max. |
| A | 0.80 | 1.00 | 0.0315 | 0.0394 | E | 2.30 | 2.50 | 0.0906 | 0.0984 |
| A1 | 0.00 | 0.10 | 0.00 | 0.0043 | E1 | 1.50 | 1.70 | 0.0590 | 0.0669 |
| b | 0.35 | 0.45 | 0.0153 | 0.0161 | E2 | 1.10 | 1.26 | 0.0433 | 0.0496 |
| c | 0.10 | 0.20 | 0.0043 | 0.0079 | L | 0.48 | 0.68 | 0.0189 | 0.0268 |
| D | 2.80 | 3.00 | 0.1102 | 0.1181 | L1 | 0.30 | 0.50 | 0.0153 | 0.0161 |
| e | 0.95 ref |  | 0.0374 ref |  | R | 0.05 | 0.15 | 0.0019 | 0.0059 |
| e1 | 1.80 | 2.00 | 0.0709 | 0.0787 | O | $0^{\circ}$ | $12^{\circ}$ | $0^{\circ}$ | $12^{\circ}$ |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

| Europe | Americas | Asia Pacific | Corporate Headquarters |
| :---: | :---: | :---: | :---: |
| Zetex GmbH | Zetex Inc | Zetex (Asia Ltd) | Zetex Semiconductors plc |
| Kustermann-park | 700 Veterans Memorial Highway | 3701-04 Metroplaza Tower 1 | Zetex Technology Park, Chadderton |
| Balanstraße 59 | Hauppauge, NY 11788 | Hing Fong Road, Kwai Fong | Oldham, OL9 9LL |
| D-81541 München | USA | Hong Kong | United Kingdom |
| Germany |  |  |  |
| Telefon: (49) 894549490 | Telephone: (1) 6313602222 | Telephone: (852) 26100611 | Telephone: (44) 1616224444 |
| Fax: (49) 8945494949 europe.sales@zetex.com | Fax: (1) 6313608222 usa.sales@zetex.com | Fax: (852) 24250494 asia.sales@zetex.com | Fax: (44) 1616224446 hq@zetex.com |

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